# Power Transistor (120V, 1.5A)

## 2SC4132 / 2SD1857

### Features

- 1) High breakdown voltage. (BVcEO = 120V)
- 2) Low collector output capacitance. (Typ. 20pF at VcB = 10V)
- 3) High transition frequency. (fT = 80MHz)
- 4) Complements the 2SB1236.

## ● **Absolute maximum ratings** (Ta = 25°C)

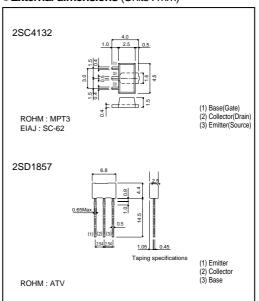
Parameter		Symbol	Limits	Unit	
Collector-base voltage		Vсво	120	V	
Collector-emitter voltage		Vceo	120	V	
Emitter-base voltage		VEBO	5	V	
Collector current		lc	2	Α	
		Icp	3	A *1	
Collector power dissipation	2SC4132		0.5	*2	
		Pc	2	w	
	2SD1857		1	1	
Junction temperature		Tj	150	°C	
Storage temperature		Tsta	-55~+150	°C	

## ● Packaging specifications and hFE

Туре	2SC4132	2SD1857
Package	MPT3	ATV
hfe	PQR	PQR
Marking	CB*	-
Code	T100	TV2
Basic ordering unit (pieces)	1000	2500

<sup>\*</sup> Denotes hre

## ●External dimensions (Units: mm)



## ● Electrical characteristics (Ta = 25°C)

Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Collector-base breakdown voltage	ВУсво	120	_	_	V	Ic = 50μA
Collector-emitter breakdown voltage	BVceo	120	-	-	V	Ic = 1mA
Emitter-base breakdown voltage	ВVево	5	-	-	V	Iε = 50μA
Collector cutoff current	Ісво	-	-	1	μА	Vcb = 100V
Emitter cutoff current	Ієво	-	-	1	μА	V <sub>EB</sub> = 4V
Collector-emitter saturation voltage	VCE(sat)	-	-	0.4	V	Ic/IB = 1A/0.1A
DC current transfer ratio	hre	82	-	390	-	Vce/lc = 5V/0.1A
Transition frequency	f⊤	-	80	-	MHz	Vce = 5V , Ie = -0.1A , f = 30MHz
Output capacitance	Cob	-	20	-	pF	Vcb = 10V , IE = 0A , f = 1MHz

<sup>\*1</sup> Single pulse Pw = 10ms \*2 When mounted on a 40 × 40 × 0.7mm ceramic board.